

### BDW94/A/B/C

### **Power Linear and Switching Applications**

- Power Darlington TR
- Complement to BDW93, BDW93A, BDW93B and BDW93C respectively



1.Base 2.Collector 3.Emitter

## **PNP Epitaxial Silicon Transistor**

## Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage		
	: BDW94	- 45	V
	: BDW94A	- 60	V
	: BDW94B	- 80	V
	: BDW94C	- 100	V
V <sub>CEO</sub>	Collector-Emitter Voltage		
	: BDW94	- 45	V
	: BDW94A	- 60	V
	: BDW94B	- 80	V
	: BDW94C	- 100	V
I <sub>C</sub>	Collector Current (DC)	- 12	А
I <sub>CP</sub>	*Collector Current (Pulse)	- 15	Α
I <sub>B</sub>	Base Current	- 0.2	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	80	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C

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Flectrical	Characteristics T <sub>C</sub> =25°C unless otherwise noted
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Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V <sub>CEO</sub> (sus)	Collector-Emitter Sustaining Voltage					
	: BDW94	$I_C = -100 \text{mA}, I_B = 0$	- 45			V
	: BDW94A		- 60			V
	: BDW94B		- 80			V
	: BDW94C		- 100			V
I <sub>CBO</sub>	Collector Cut-off Current					
	: BDW94	$V_{CB} = -45V, I_{E} = 0$			- 100	μΑ
	: BDW94A	$V_{CB} = -60V, I_{E} = 0$			- 100	μΑ
	: BDW94B	$V_{CB} = -80V, I_{E} = 0$			- 100	μΑ
	: BDW94C	$V_{CB} = -100V, I_{E} = 0$			- 100	μΑ
I <sub>CEO</sub>	Collector Cut-off Current					
	: BDW94	$V_{CE} = -45V, I_{B} = 0$			-1	mA
	: BDW94A	$V_{CE} = -60V, I_{B} = 0$			- 1	mA
	: BDW94B	$V_{CE} = -80V, I_{B} = 0$			- 1	mA
	: BDW94C	$V_{CE} = -100V, I_{B} = 0$			- 1	mA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$			- 2	mA
h <sub>FE</sub>	* DC Current Gain	$V_{CE} = -3V, I_{C} = -3A$	1000			
		$V_{CE} = -3V, I_{C} = -5A$	750		20000	
		$V_{CE} = -3V, I_{C} = -10A$	100			
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	$I_C = -5A, I_B = -20mA$			- 2	V
		$I_C = -10A$ , $I_B = -100mA$			- 3	V
V <sub>BE</sub> (sat)	* Base-Emitter Saturation Voltage	$I_C = -5A, I_B = -20mA$			- 2.5	V
		$I_C = -10A$ , $I_B = -100mA$			- 4	V
V <sub>F</sub>	* Parallel Diode Forward Voltage	I <sub>F</sub> = - 5A		- 1.3	- 2	V
		I <sub>F</sub> = -1 0A		- 1.8	- 4	V

<sup>\*</sup> Pulse Test: PW=300µs, duty Cycle =1.5% Pulsed

# **Typical Characteristics**

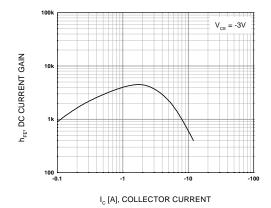


Figure 1. DC Current Gain

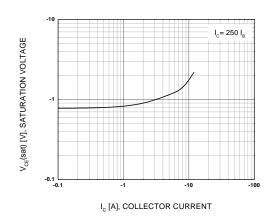


Figure 2. Collector-Emitter Saturation Voltage

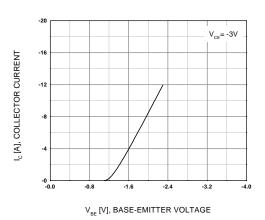


Figure 3. Base-Emitter On Voltage

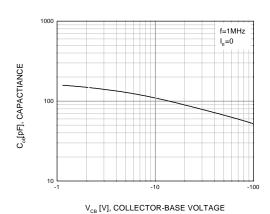


Figure 4. Output Capacitance

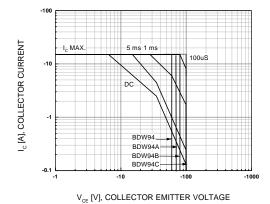


Figure 5. Safe Operating Area

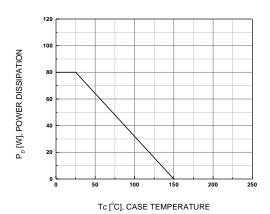
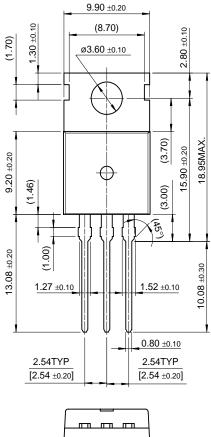


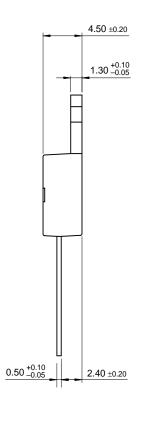
Figure 6. Power Derating

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# **Package Demensions**

## TO-220





10.00 ±0.20

Dimensions in Millimeters

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